

Hex Buffer

MC74LVX50

The MC74LVX50 is an advanced high speed CMOS buffer fabricated with silicon gate CMOS technology.

The internal circuit is composed of three stages, including a buffered output which provides high noise immunity and stable output. The inputs tolerate voltages up to 6.5 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 4.1 \text{ ns}$ (Typ) at $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu\text{A}$ (Max) at $T_A = 25^\circ\text{C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 3.6 V Operating Range
- Low Noise: $V_{OLP} = 0.5 \text{ V}$ (Max)
- These Devices are Pb-Free and are RoHS Compliant

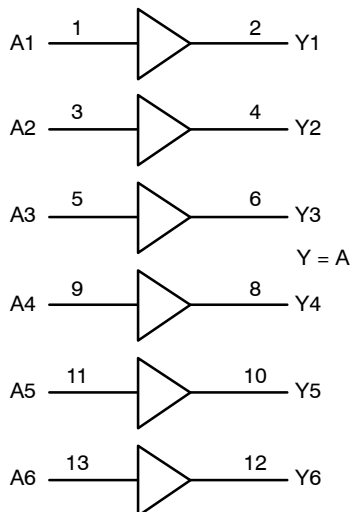


Figure 1. Logic Diagram

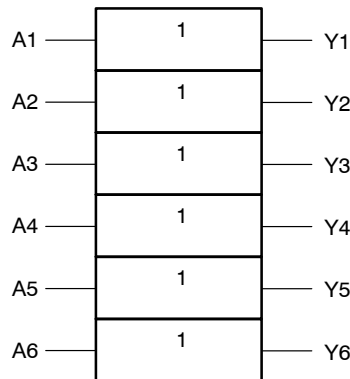


Figure 2. Logic Symbol

FUNCTION TABLE

A Input	Y Output
L	L
H	H

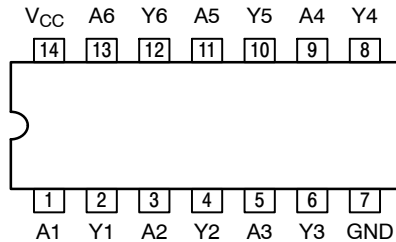


SOIC-14 NB
D SUFFIX
CASE 751A



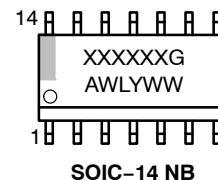
TSSOP-14
DT SUFFIX
CASE 948G

PIN ASSIGNMENT

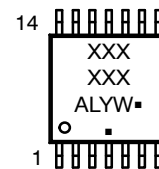


14-Lead (Top View)

MARKING DIAGRAMS



SOIC-14 NB



TSSOP-14

XXX = Specific Device Code
A = Assembly Location
WL, L = Wafer Lot
Y = Year
WW, W = Work Week
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MC74LVX50

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	− 0.5 to +6.5	V
V _{IN}	DC Input Voltage	− 0.5 to +6.5	V
V _{OUT}	DC Output Voltage	− 0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current V _I < GND	− 20	mA
I _{OK}	DC Output Diode Current V _O < GND	±20	mA
I _{OUT}	DC Output Sink Current	±25	mA
I _{CC}	DC Supply Current per Supply Pin	±50	mA
T _{STG}	Storage Temperature Range	− 65 to + 150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
T _J	Junction Temperature under Bias	+ 150	°C
θ _{JA}	Thermal Resistance (Note 1)	SOIC TSSOP 116 150	°C/W
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 30% – 35%	UL 94–V0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Charged Device Model (Note 3) > 2000 2000	V V
I _{Latchup}	Latchup Performance	Above V _{CC} and Below GND at 85°C (Note 4)	±300 mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
2. Tested to EIA/JESD22–A114–A.
3. Tested to JESD22–C101–A.
4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Supply Voltage	2.0	3.6	V
V _I	Input Voltage (Note 5)	0	5.5	V
V _O	Output Voltage (HIGH or LOW State)	0	V _{CC}	V
T _A	Operating Free–Air Temperature	− 40	+ 85	°C
Δt/ΔV	Input Transition Rise or Fall Rate	V _{CC} = 3.0 V ±0.3 V		ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

5. Unused inputs may not be left open. All inputs must be tied to a high– or low–logic input voltage level.

NOTE: The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

MC74LVX50

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} (V)	T _A = 25°C			T _A ≤ 85°C		Unit
				Min	Typ	Max	Min	Max	
V _{IH}	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V _{OH}	High-Level Output Voltage (V _{IN} = V _{IH} or V _{IL})	I _{OH} = -50 μA I _{OH} = -50 μA I _{OH} = -4 mA	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}	Low-Level Output Voltage (V _{IN} = V _{IH} or V _{IL})	I _{OL} = 50 μA I _{OL} = 50 μA I _{OL} = 4 mA	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 3.6			±0.1		±1.0	μA
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	3.6			2.0		20.0	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS Input t_r = t_f = 3.0 ns

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A ≤ 85°C		Unit
			Min	Typ	Max	Min	Max	
t _{PLH} , t _{PHL}	Propagation Delay, Input A to Y	V _{CC} = 2.7 V C _L = 15 pF C _L = 50 pF		5.4 7.9	10.1 13.6	1.0 1.0	12.5 16.0	ns
		V _{CC} = 3.3 V ± 0.3 V C _L = 15 pF C _L = 50 pF		4.1 6.6	6.2 9.7	1.0 1.0	7.5 11.5	
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 6)	V _{CC} = 2.7 V C _L = 50 pF			1.5		1.5	ns
		V _{CC} = 3.3 V ±0.3V C _L = 50 pF			1.5		1.5	
C _{IN}	Input Capacitance			4	10		10	pF
C _{PD}	Power Dissipation Capacitance (Note 7)	Typical @ 25°C, V _{CC} = 3.3 V						pF
		15						

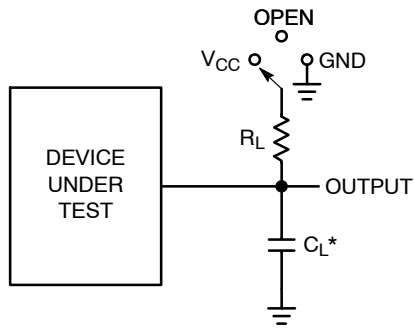
6. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

7. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS Input t_r = t_f = 3.0ns, C_L = 50pF, V_{CC} = 3.3 V

Symbol	Characteristic	T _A = 25°C		Unit
		Typ	Max	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.5	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.5	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

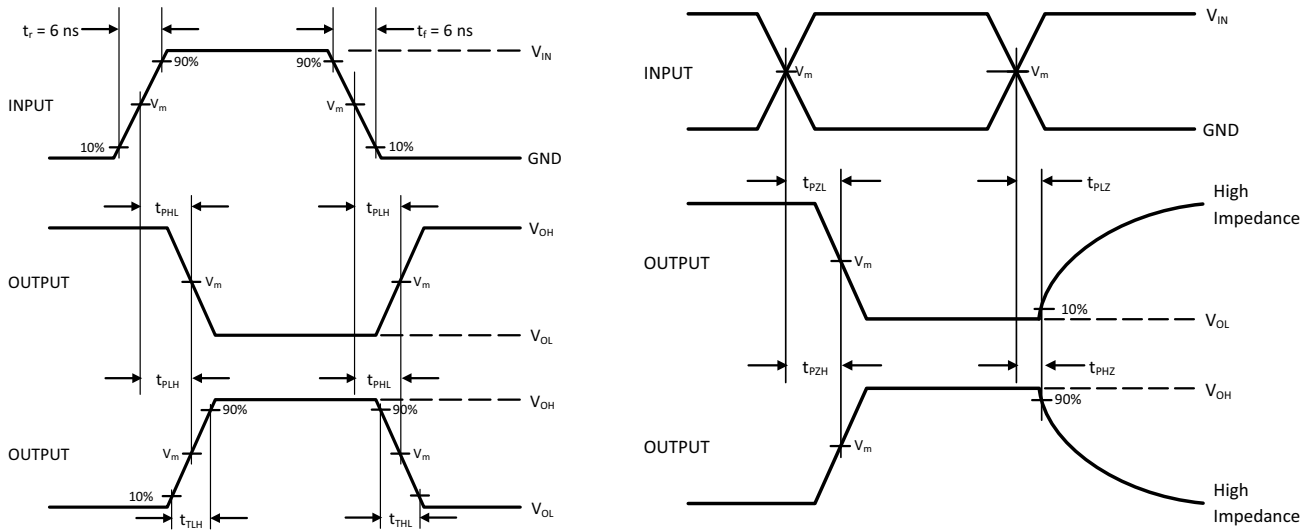
MC74LVX50



*C_L Includes probe and jig capacitance

Test	Switch Position	C _L	R _L
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table	1 kΩ
t _{PLZ} / t _{PZL}	V _{CC}		
t _{PHZ} / t _{PZH}	GND		

Figure 3. Test Circuit



Device	V _{IN} , V	V _m , V
MC74LVX50	V _{CC}	50% x V _{CC}

Figure 4. Switching Waveforms

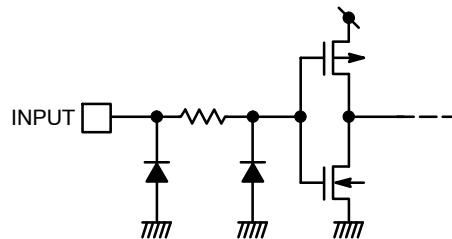


Figure 5. Input Equivalent Circuit

MC74LVX50

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MC74LVX50DR2G	LVX50	SOIC-14	2500 Tape & Reel
MC74LVX50DTG	LVX 50	TSSOP-14	96 Units / Rail
MC74LVX50DTR2G	LVX 50	TSSOP-14	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SOIC-14 NB
CASE 751A-03
ISSUE L

DATE 03 FEB 2016

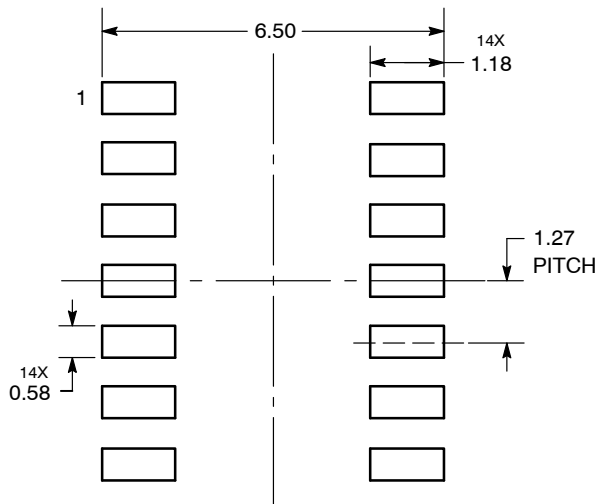


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0°	7°	0°	7°

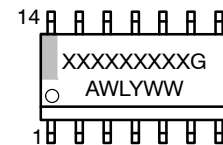
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC
MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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CASE 751A-03
ISSUE L

DATE 03 FEB 2016

STYLE 1:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 2:
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION
2. ANODE
3. ANODE
4. NO CONNECTION
5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

STYLE 4:
PIN 1. NO CONNECTION
2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
8. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 5:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. ANODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
2. COMMON ANODE
3. COMMON CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. ANODE/CATHODE
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. COMMON CATHODE
12. COMMON ANODE
13. ANODE/CATHODE
14. ANODE/CATHODE

STYLE 8:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
12. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

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TSSOP-14 WB
CASE 948G
ISSUE C

DATE 17 FEB 2016

SCALE 2:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

RECOMMENDED
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC
MARKING DIAGRAM*



A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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